

**Silicon PNP Power Transistors****2SA1264N****DESCRIPTION**

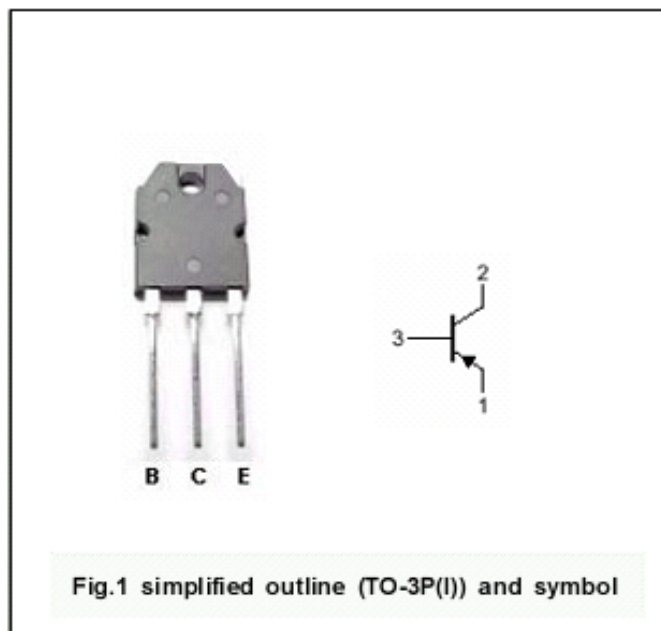
- With TO-3P(I) package
- Complement to type 2SC3181N
- 2SA1264 with short pin

**APPLICATIONS**

- Power amplifier applications

**PINNING**

| PIN | DESCRIPTION                           |
|-----|---------------------------------------|
| 1   | Emitter                               |
| 2   | Collector; connected to mounting base |
| 3   | Base                                  |

**Absolute maximum ratings(Ta=25℃)**

| SYMBOL    | PARAMETER                 | CONDITIONS             | VALUE   | UNIT |
|-----------|---------------------------|------------------------|---------|------|
| $V_{CBO}$ | Collector-base voltage    | Open emitter           | -120    | V    |
| $V_{CEO}$ | Collector-emitter voltage | Open base              | -120    | V    |
| $V_{EBO}$ | Emitter-base voltage      | Open collector         | -5      | V    |
| $I_C$     | Collector current         |                        | -8      | A    |
| $I_B$     | Base current              |                        | -0.8    | A    |
| $P_T$     | Total power dissipation   | $T_C=25^\circ\text{C}$ | 80      | W    |
| $T_J$     | Junction temperature      |                        | 150     | ℃    |
| $T_{stg}$ | Storage temperature       |                        | -55~150 | ℃    |



## Silicon PNP Power Transistors

## 2SA1264N

## CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

| SYMBOL               | PARAMETER                            | CONDITIONS                                       | MIN  | TYP. | MAX  | UNIT |
|----------------------|--------------------------------------|--------------------------------------------------|------|------|------|------|
| V <sub>(BR)CEO</sub> | Collector-emitter breakdown voltage  | I <sub>C</sub> =-50mA, I <sub>B</sub> =0         | -120 |      |      | V    |
| V <sub>CEsat</sub>   | Collector-emitter saturation voltage | I <sub>C</sub> =-6A; I <sub>B</sub> =-0.6A       |      |      | -2.0 | V    |
| V <sub>BE</sub>      | Base-emitter voltage                 | I <sub>C</sub> =-4A; V <sub>CE</sub> =-5V        |      |      | -1.5 | V    |
| I <sub>CBO</sub>     | Collector cut-off current            | V <sub>CB</sub> =-120V; I <sub>E</sub> =0        |      |      | -5   | μA   |
| I <sub>EBO</sub>     | Emitter cut-off current              | V <sub>EB</sub> =-5V; I <sub>C</sub> =0          |      |      | -5   | μA   |
| h <sub>FE-1</sub>    | DC current gain                      | I <sub>C</sub> =-1A; V <sub>CE</sub> =-5V        | 55   |      | 160  |      |
| h <sub>FE-2</sub>    | DC current gain                      | I <sub>C</sub> =-4A; V <sub>CE</sub> =-5V        | 35   |      |      |      |
| f <sub>T</sub>       | Transition frequency                 | I <sub>C</sub> =-1A; V <sub>CE</sub> =-5V        |      | 30   |      | MHz  |
| C <sub>ob</sub>      | Output capacitance                   | I <sub>E</sub> =0; V <sub>CB</sub> =-10V; f=1MHz |      | 420  |      | pF   |

◆ h<sub>FE-1</sub> Classifications

| R      | O      |
|--------|--------|
| 55-110 | 80-160 |



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PACKAGE OUTLINE

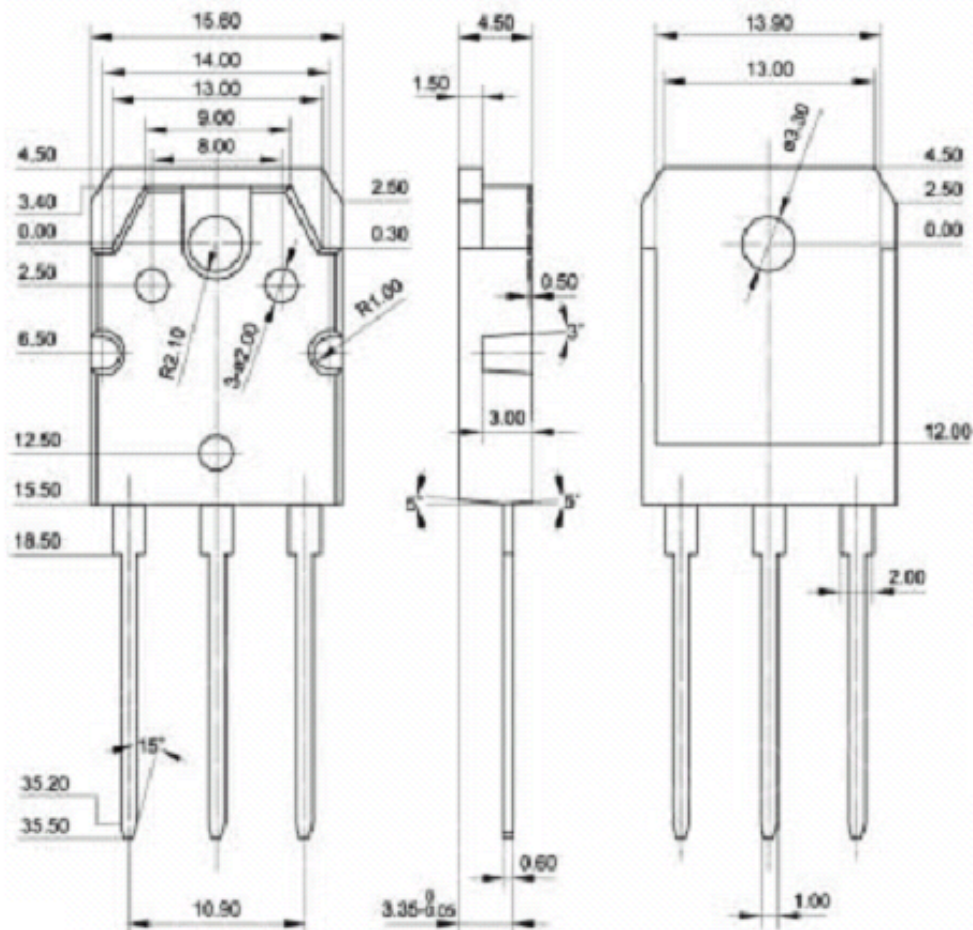


Fig.2 Outline dimensions (unindicated tolerance:  $\pm 0.10$  mm)



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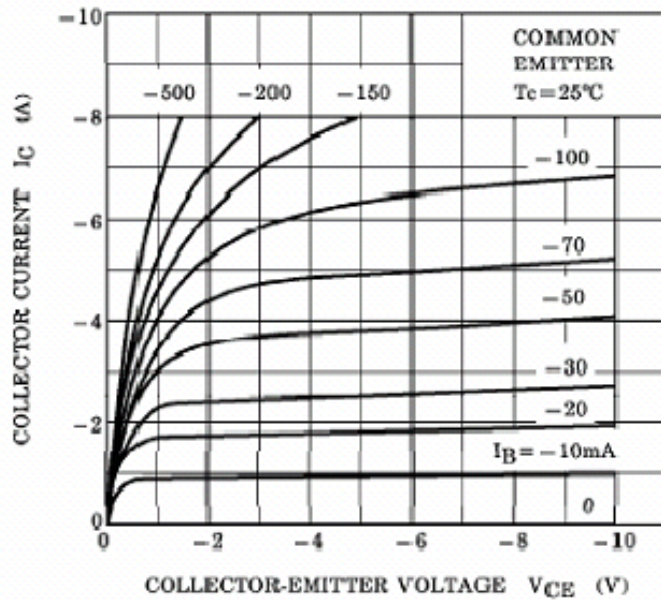


Fig.3 Static Characteristic

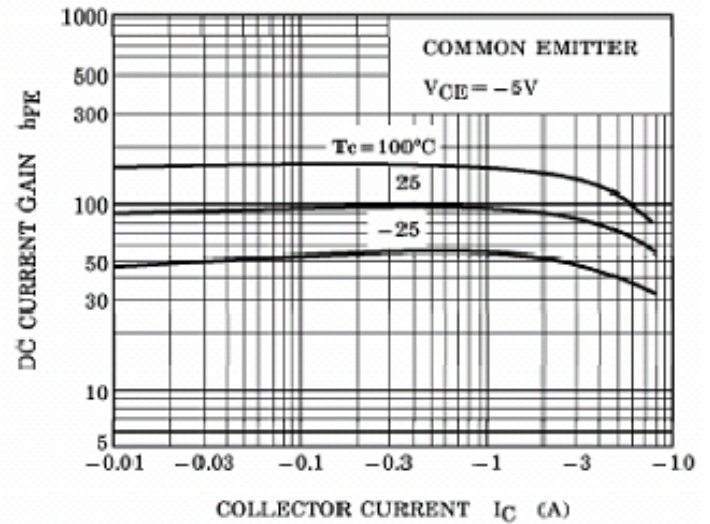


Fig.4 DC current Gain

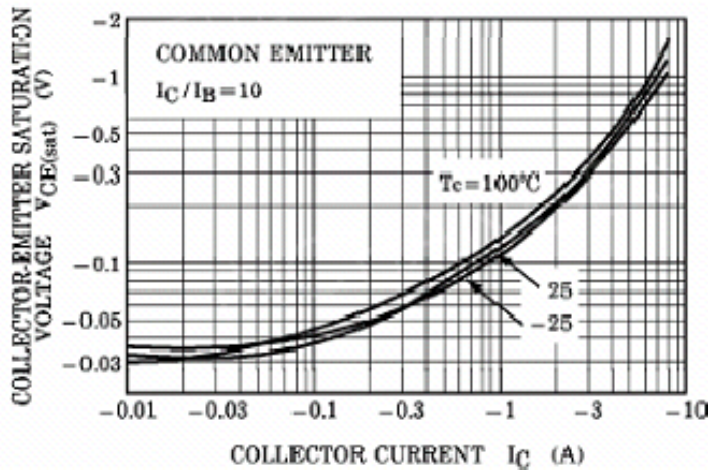


Fig.5 Collector-Emitter Saturation Voltage

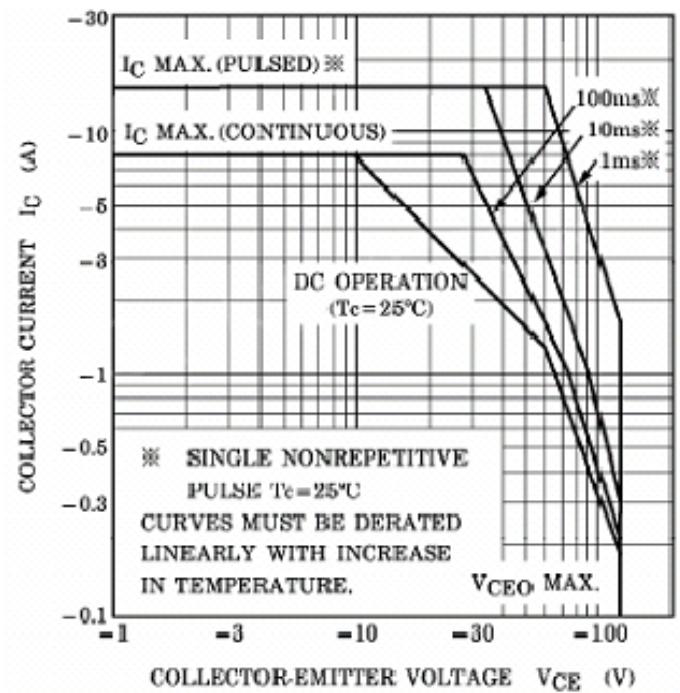


Fig.6 Safe Operating Area